5-inch Wafer and Strip Plating Line Conversion for Automotive Grade S2A~S2M

DESCRIPTION OF CHANGE: Vishay Diodes Division will change wafer diameter from 4 inch to 5 inch for Standard Rectifier in SMB package. Beside this wafer diameter change, the plating method for lead finishing will be converted from barrel to strip plating to improve plating thickness uniformity. Qualification test has been confirmed to meet and pass all specifications for automotive grade. There will be no change in form, fit or function of final products.

CLASSIFICATION OF CHANGE: Wafer diameter as well as Plating scheme

REASON FOR CHANGE: Capacity expansion and delivery improvement

EXPECTED INFLUENCE ON QUALITY/RELIABILITY/PERFORMANCE: Better plating thickness uniformity, no change in other quality and reliability performance.

PRODUCT CATEGORY: Rectifier

PART NUMBERS/SERIES/FAMILIES AFFECTED: Involved part numbers are listed in below table.

<table>
<thead>
<tr>
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<tbody>
<tr>
<td>S2AHE3/52T</td>
<td>S2AHE3_A/H</td>
<td>S2G-6600HE3J/5BT</td>
<td>S2G-6600HE3J_A/I</td>
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<td>S2AHE3_A/I</td>
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<tr>
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<td>S2B-002HE3_A/I</td>
<td>S2GHE3/5BT</td>
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<td>S2J-6600HE3/52T</td>
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<td>S2MHE3/5BT</td>
<td>S2MHE3_A/I</td>
</tr>
</tbody>
</table>

VISHAY BRAND: Vishay General Semiconductor

TIME SCHEDULE:
Start conversion date: June 15, 2015
Last time buy of existing P/N: October 15, 2015
Last time ship of existing P/N: April 15, 2016
SAMPLE AVAILABILITY: Available upon request

PRODUCT IDENTIFICATION: Adding underscore (_ ) + revision code “A” following base part number as the identification. Meanwhile, the package code will be simplified as communicated already in Fast Fact #FF-DD-001-2012 issued on December 3, 2012.

QUALIFICATION DATA: Available upon request

RESPONSE DATE: This PCN is considered approved, without further notification, unless we receive specific customer concerns before June 7, 2015 or as specified by contract.

ISSUED BY: RS Chin, Product Marketing Director – Rectifier (Standard & Schottky)

For further information, please contact your regional Vishay office.

Contact Information:

The Americas
Vishay Semiconductors
150 Motor Parkway, Suite 101E
Hauppauge, NY 11788 USA
Phone : 631 300 3816
Fax : 631 300 3843
Diodes-Americas@vishay.com

Europe
Vishay Semiconductors
Theresienstrasse 2
D-74072 Heilbronn, Germany
Phone : +49 7131 67 3364 (or 3365)
Fax: +49 7131 67 2938
Diodes-Europe@vishay.com

Asia/Pacific
Vishay Semiconductors
15D, Sun Tong Infoport Plaza
55 Huai Hai West Road, Shanghai, China
Phone: +86 138 1787 2112
Fax: +86 21 5258 7979
Diodes-Asia@vishay.com